

Multi-Layer Nanoelectromechanical (NEM) Memory

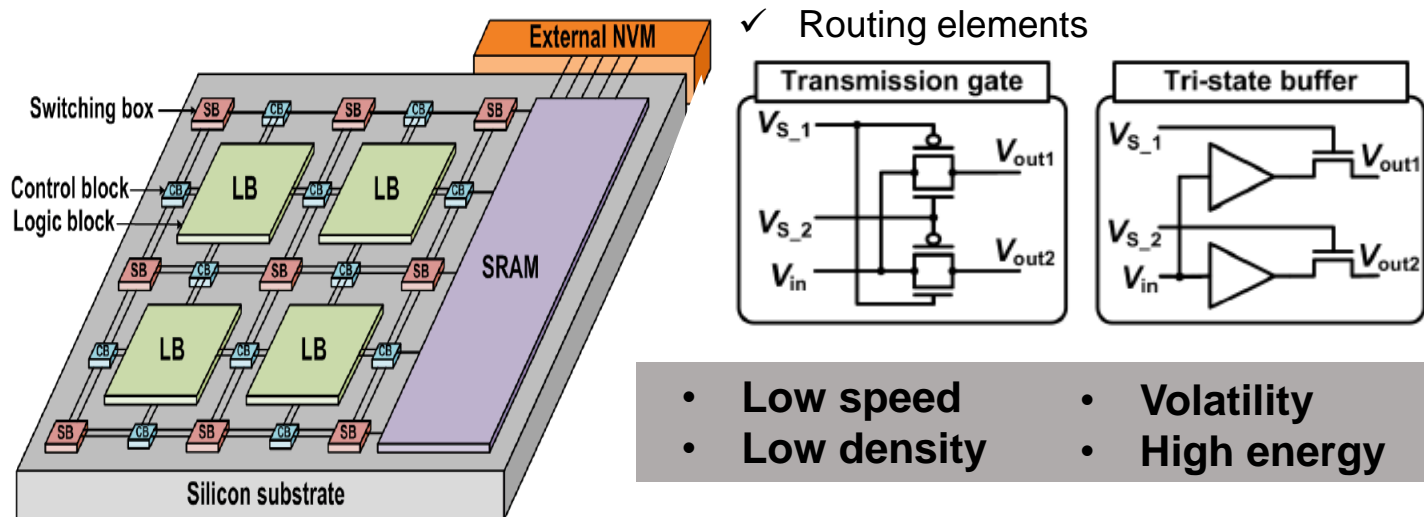
Switches for Efficient Routing Operation

윤지수 (삼차원 집적 및 소자 연구실)

SOGANG UNIVERSITY

Motivation (1)

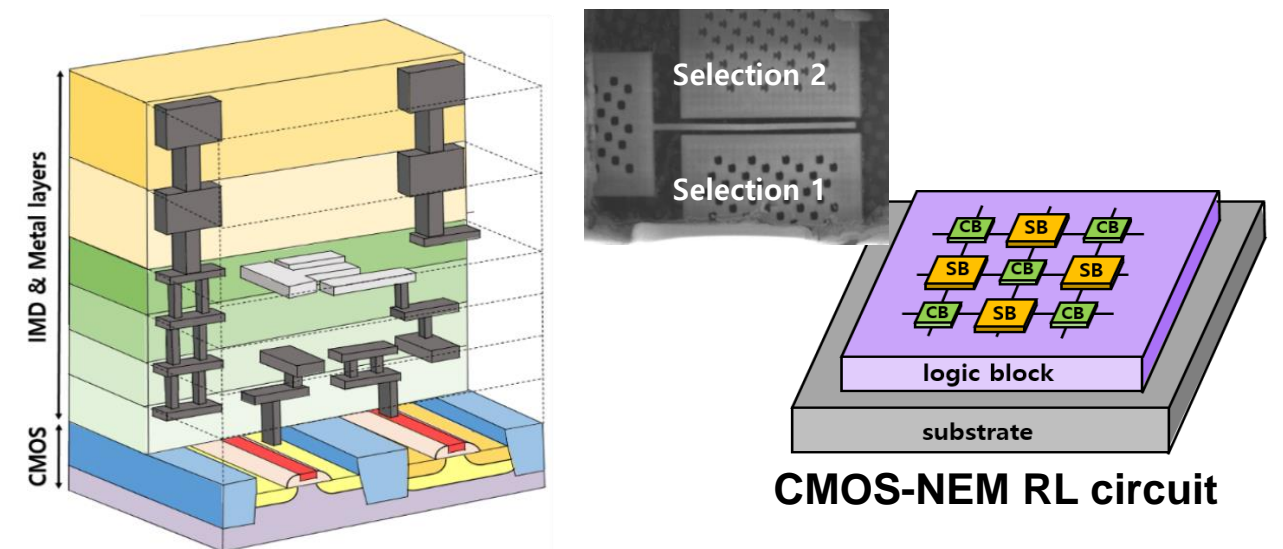
- RL such as FPGA, CPLD consists of logic blocks and routing elements
- In conventional RL case, routing operation consumes ~ 80% of chip area, ~ 80% of core power and ~ 75% total delay



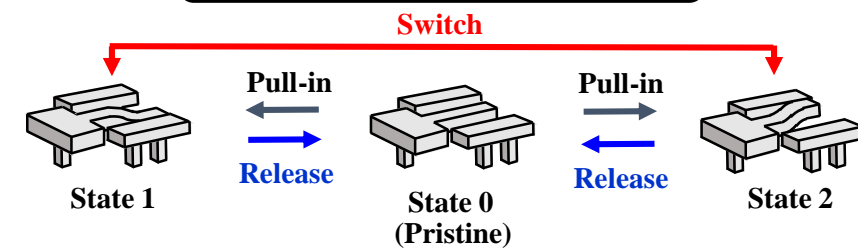
Need to decrease chip area, power consumption and delay

Motivation (2)

- Replace routing elements from CMOS-only to NEM memory switch at single metal layer
- Routing elements located at BEOL

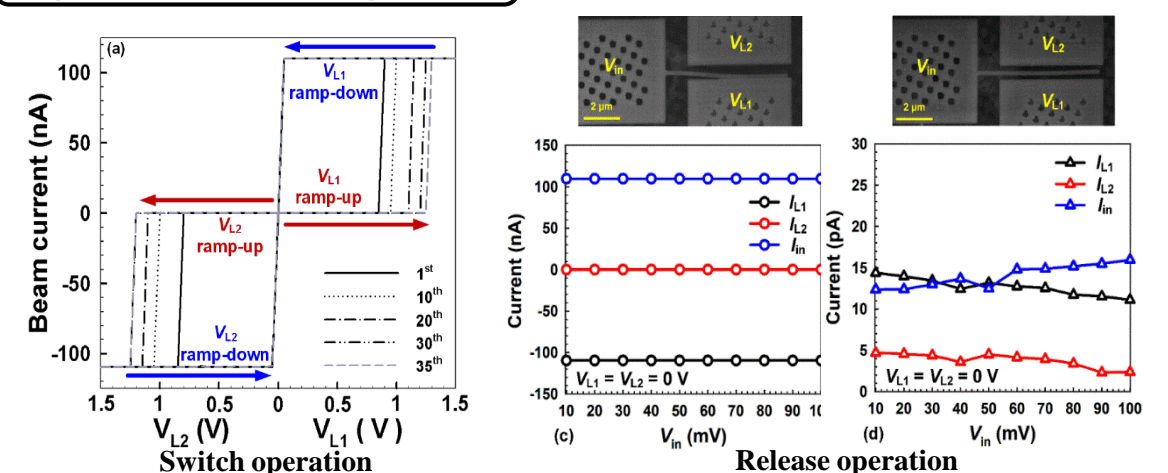


Operation of NEM memory switch

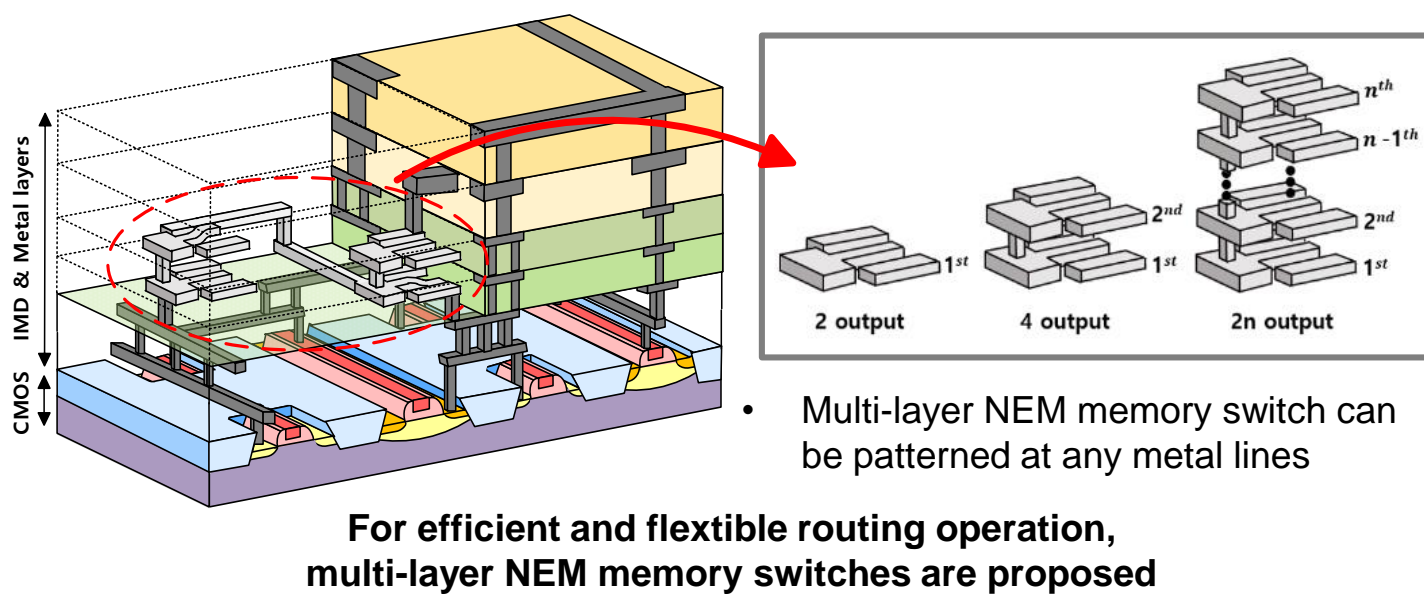


- High speed
- High density
- Non-Volatility
- Low energy

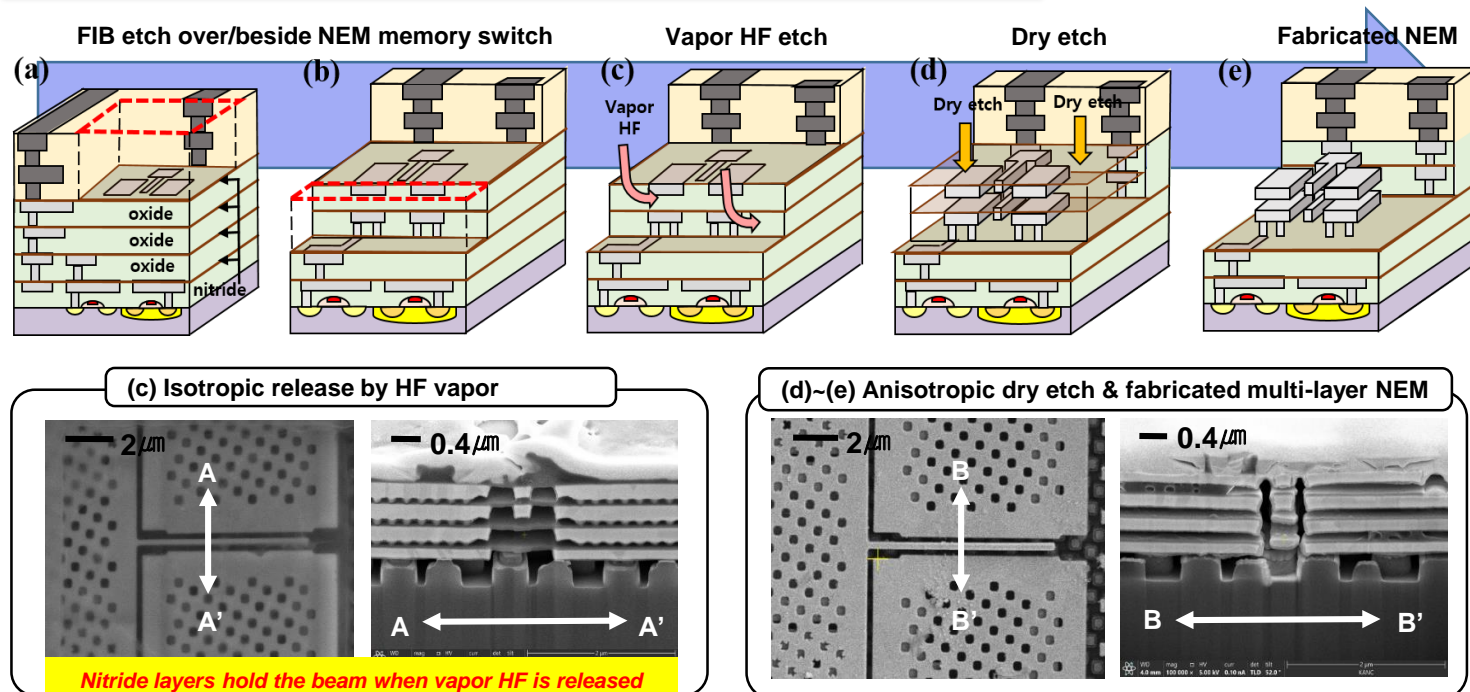
Experimental results of operation



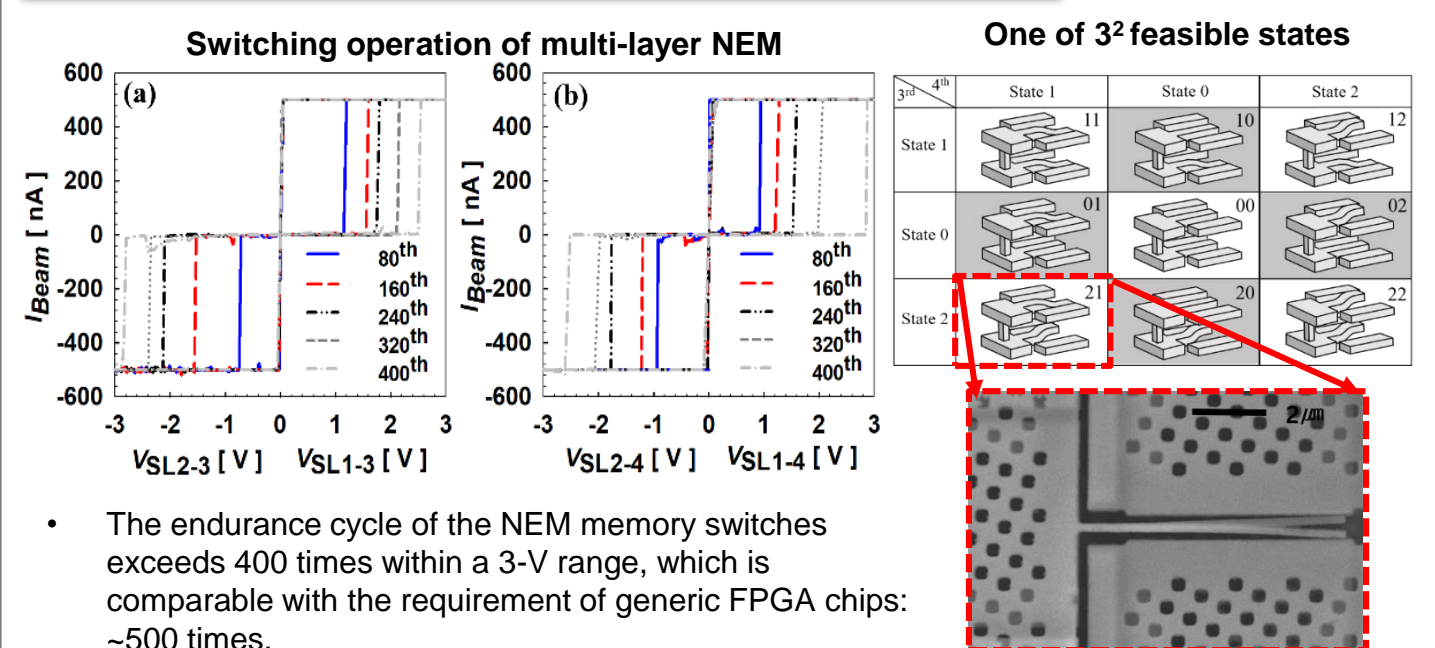
Ideas



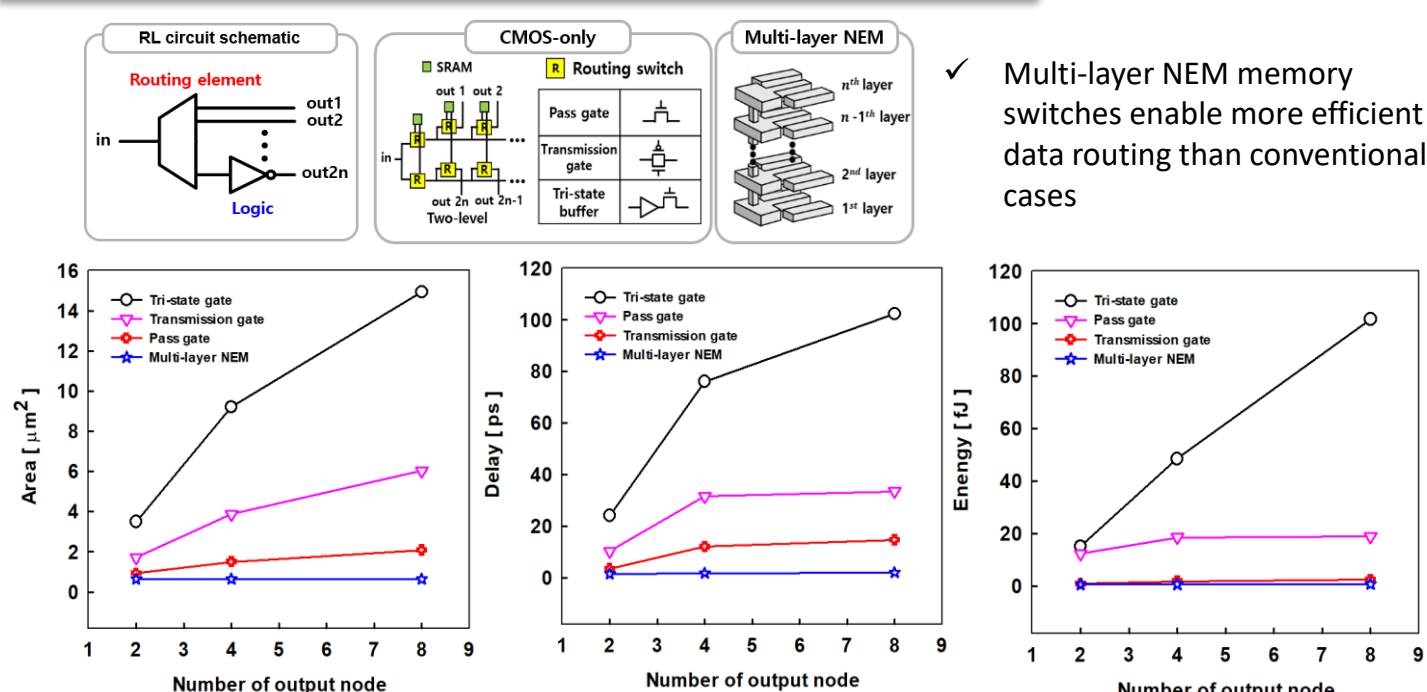
Fabrication process



Experimental Results



Simulation Results



Conclusion

- Multi-layer NEM memory switches integrated vertically over CMOS baseline circuits were experimentally demonstrated using a 65-nm CMOS baseline process
- By fabrication process, the throughput of NEM memory switch is increased than before process.
- The area, energy and power of multi-layer NEM memory switches are superior to CMOS-only routing elements
- An n -layer NEM memory switches can implement 3^n states which can be used for a $2n$ -to-1 multiplexer or 1-to- $2n$ de-multiplexer